

(NOTE:For new designs, we recommend IR's new product IRS21531D)

IR21531(D)(S) &(PbF)

# SELF-OSCILLATING HALF-BRIDGE DRIVER

#### **Features**

- Integrated 600V half-bridge gate driver
- 15.6V zener clamp on Vcc
- True micropower start up
- Tighter initial deadtime control
- Low temperature coefficient deadtime
- Shutdown feature (1/6th Vcc) on C⊤ pin
- Increased undervoltage lockout Hysteresis (1V)
- Lower power level-shifting circuit
- Constant LO, HO pulse widths at startup
- Lower di/dt gate driver for better noise immunity
- Low side output in phase with RT
- Internal 50nsec (typ.) bootstrap diode (IR21531D)
- Excellent latch immunity on all inputs and outputs
- ESD protection on all leads
- Also available LEAD-FREE

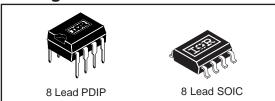
# **Description**

The IR21531D(S) are an improved version of the popular IR2155 and IR2151 gate driver ICs, and incor-

### **Product Summary**

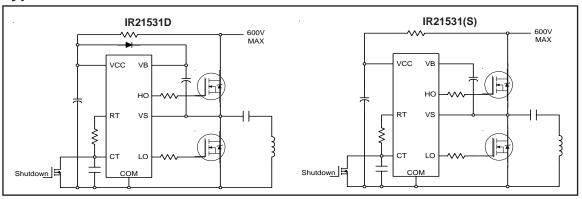
Voffset	600V max.
Duty Cycle	50%
T <sub>r</sub> /T <sub>p</sub>	80/40ns
V <sub>clamp</sub>	15.6V
Deadtime (typ.)	0.6 µs

## **Packages**



porates a high voltage half-bridge gate driver with a front end oscillator similar to the industry standard CMOS 555 timer. The IR21531 provides more functionality and is easier to use than previous ICs. A shutdown feature has been designed into the C<sub>T</sub> pin, so that both gate driver outputs can be disabled using a low voltage control signal. In addition, the gate driver output pulse widths are the same once the rising undervoltage lockout threshold on V<sub>CC</sub> has been reached, resulting in a more stable profile of frequency vs time at startup. Noise immunity has been improved significantly, both by lowering the peak di/dt of the gate drivers, and by increasing the undervoltage lockout hysteresis to 1V. Finally, special attention has been payed to maximizing the latch immunity of the device, and providing comprehensive ESD protection on all pins.

#### **Typical Connections**



# IR21531(D)(S) & (PbF) NOTE:For new designs, we recommend IR's new product IRS21531D

# **Absolute Maximum Ratings**

Absolute maximum ratings indicate sustained limits beyond which damage to the device may occur. All voltage parameters are absolute voltages referenced to COM, all currents are defined positive into any lead. The thermal resistance and power dissipation ratings are measured under board mounted and still air conditions.

Symbol	Definition	Min.	Max.	Units	
V <sub>B</sub>	High side floating supply voltage		-0.3	625	
Vs	High side floating supply offset voltage		V <sub>B</sub> - 25	V <sub>B</sub> + 0.3	
V <sub>HO</sub>	High side floating output voltage		V <sub>S</sub> - 0.3	V <sub>B</sub> + 0.3	Ī ,,
V <sub>LO</sub>	Low side output voltage		-0.3	V <sub>CC</sub> + 0.3	V
V <sub>RT</sub>	R <sub>T</sub> pin voltage		-0.3	V <sub>CC</sub> + 0.3	
V <sub>CT</sub>	C <sub>T</sub> pin voltage	-0.3	V <sub>CC</sub> +0.3		
Icc	Supply current (note 1)	_	25	mA	
I <sub>RT</sub>	R <sub>T</sub> pin current		-5	5	
dV <sub>S</sub> /dt	Allowable offset voltage slew rate		-50	50	V/ns
PD	Maximum power dissipation @ T <sub>A</sub> ≤ +25°C	(8 Lead DIP)	_	1.0	W
		(8 Lead SOIC)	_	0.625	T VV
Rth <sub>JA</sub>	Thermal resistance, junction to ambient	(8 Lead DIP)	_	125	°C/W
	(8 Lead SOIC)		_	200	- C/VV
TJ	Junction temperature		-55	150	
T <sub>S</sub>	Storage temperature	-55	150	°C	
TL	Lead temperature (soldering, 10 seconds)		_	300	

### **Recommended Operating Conditions**

For proper operation the device should be used within the recommended conditions.

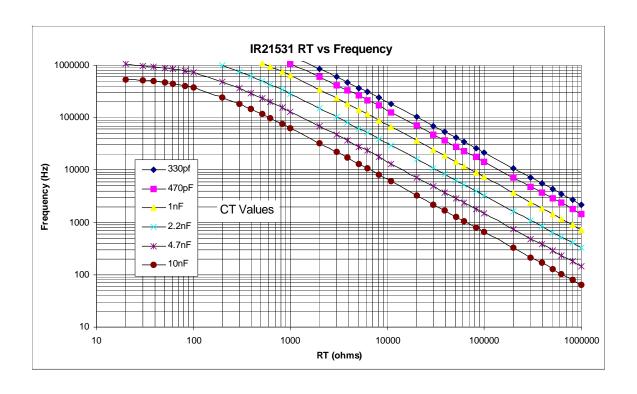
Symbol	Definition	Min.	Max.	Units
V <sub>BS</sub>	High side floating supply voltage	V <sub>CC</sub> - 0.7	VCLAMP	
Vs	Steady state high side floating supply offset voltage	-3.0 (note 2)	600	V
Vcc	Supply voltage	10	VCLAMP	
Icc	Supply current	(note 3)	5	mA
TJ	Junction temperature	-40	125	°C

- Note 1: This IC contains a zener clamp structure between the chip V<sub>CC</sub> and COM which has a nominal breakdown voltage of 15.6V. Please note that this supply pin should not be driven by a DC, low impedance power source greater than the V<sub>CLAMP</sub> specified in the Electrical Characteristics section.
- Note 2: Care should be taken to avoid output switching conditions where the V<sub>S</sub> node flies inductively below ground by more than 5V
- Note 3: Enough current should be supplied to the V<sub>CC</sub> pin of the IC to keep the internal 15.6V zener diode clamping the voltage at this pin.



# **Recommended Component Values**

Symbol	Component	Min.	Max.	Units
R <sub>T</sub>	Timing resistor value	10	_	kΩ
C <sub>T</sub>	C <sub>T</sub> pin capacitor value	330	_	pF



# IR21531(D)(S) & (PbF) NOTE:For new designs, we recommend IR's new product IRS21531D

#### **Electrical Characteristics**

 $V_{BIAS}$  ( $V_{CC}$ ,  $V_{BS}$ ) = 12V,  $C_L$  = 1000 pF,  $C_T$  = 1 nF and  $T_A$  = 25°C unless otherwise specified. The  $V_{IN}$ ,  $V_{TH}$  and  $I_{IN}$  parameters are referenced to COM. The  $V_O$  and  $I_O$  parameters are referenced to COM and are applicable to the respective output leads: HO or LO.

Low Voltage Supply Characteristics								
Symbol	Definition	Min.	Тур.	Max.	Units	Test Conditions		
V <sub>CCUV+</sub>	Rising V <sub>CC</sub> undervoltage lockout threshold	8.1	9.0	9.9				
V <sub>CCUV</sub> -	Falling V <sub>CC</sub> undervoltage lockout threshold	7.2	8.0	8.8	V			
VCCUVH	V <sub>CC</sub> undervoltage lockout Hysteresis	0.5	1.0	1.5				
I <sub>QCCUV</sub> Micropower startup V <sub>CC</sub> supply current		_	75	150	μА	V <sub>CC</sub> ≤V <sub>CCUV</sub> -		
IQCC	Quiescent V <sub>CC</sub> supply current	_	500	950	μΑ			
VCLAMP	V <sub>CC</sub> zener clamp voltage	14.4	15.6	16.8	V	I <sub>CC</sub> = 5mA		

# Floating Supply Characteristics

Symbol	Definition	Min.	Тур.	Max.	Units	Test Conditions
I <sub>QBSUV</sub>	Micropower startup V <sub>BS</sub> supply current	_	0	10	μА	Vcc≤Vccuv-
I <sub>QBS</sub>	Quiescent VBS supply current	_	30	50	μΑ	
V <sub>BSMIN</sub>	Minimum required V <sub>BS</sub> voltage for proper	_	4.0	5.0	V	V <sub>CC</sub> =V <sub>CCUV+</sub> + 0.1V
	functionality from R <sub>T</sub> to HO					
I <sub>LK</sub>	Offset supply leakage current	_	_	50	μΑ	$V_{B} = V_{S} = 600V$
VF	Bootstrap diode forward voltage (IR2153D)	0.5	_	1.2	V	IF = 250mA

#### Oscillator I/O Characteristics

Symbol	Definition	Min.	Тур.	Max.	Units	<b>Test Conditions</b>	
fosc	Oscillator frequency	19.4	20	20.6	kHz	$R_T = 36.9k\Omega$	
		94	100	106	KITZ	$RT = 7.43k\Omega$	
d	RT pin duty cycle	48	50	52	%	fo < 100kHz	
I <sub>CT</sub>	C <sub>T</sub> pin current	_	0.001	1.0	uA		
I <sub>CTUV</sub>	UV-mode C <sub>T</sub> pin pulldown current	0.30	0.70	1.2	mA	$V_{CC} = 7V$	
VcT+	Upper C⊤ ramp voltage threshold	_	8.0	_			
Vcт-	Lower C <sub>T</sub> ramp voltage threshold	_	4.0	_	V		
VCTSD	CT voltage shutdown threshold	1.8	2.1	2.4	Ī		
V <sub>RT+</sub>	High-level RT output voltage, VCC - VRT	_	10	50		I <sub>RT</sub> = 100μA	
		_	100	300		I <sub>RT</sub> = 1mA	
VRT-	Low-level R <sub>T</sub> output voltage	_	10	50		I <sub>RT</sub> = 100μA	
		_	100	300	mV	I <sub>RT</sub> = 1mA	
VRTUV	UV-mode R <sub>T</sub> output voltage	_	0	100	IIIV	V <sub>CC</sub> ≤ V <sub>CCUV</sub> -	
VRTSD	SD-Mode RT output voltage, Vcc - VRT	_	10	50		$I_{RT} = 100 \mu A$ ,	
						V <sub>CT</sub> = 0V	
		_	10	300	1	$I_{RT} = 1mA$ ,	
						V <sub>CT</sub> = 0V	

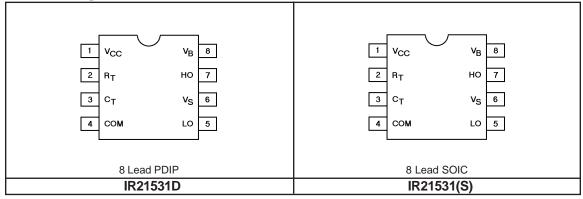
# **Electrical Characteristics (cont.)**

Gate D	Gate Driver Output Characteristics								
Symbol	Definition	Min.	Тур.	Max.	Units	<b>Test Conditions</b>			
VoH	High level output voltage, V <sub>BIAS</sub> -V <sub>O</sub>		0	100		I <sub>O</sub> = OA			
VOL	Low-level output voltage, VO	_	0	100	mV	I <sub>O</sub> = OA			
VOL_UV	UV-mode output voltage, VO	_	0	100	1111	I <sub>O</sub> = OA			
						$I_O = OA$ $V_{CC} \le V_{CCUV}$			
tr	Output rise time	_	80	150					
tf	Output fall time	_	45	100	nsec				
t <sub>sd</sub>	Shutdown propogation delay	_	660	_	1				
td	Output deadtime (HO or LO)	0.35	0.60	0.85	μsec				

#### **Lead Definitions**

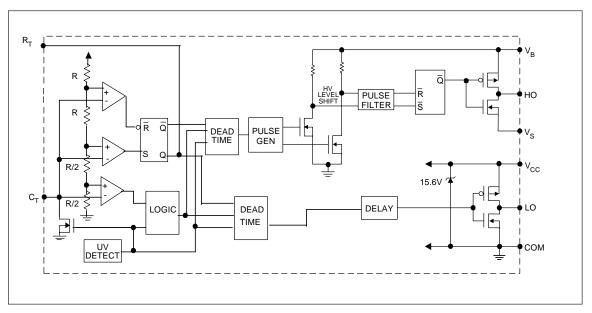
Symbol	Description
Vcc	Logic and internal gate drive supply voltage
R <sub>T</sub>	Oscillator timing resistor input
C <sub>T</sub>	Oscillator timing capacitor input
COM	IC power and signal ground
LO	Low side gate driver output
VS	High voltage floating supply return
НО	High side gate driver output
V <sub>B</sub>	High side gate driver floating supply

**Lead Assignments** 

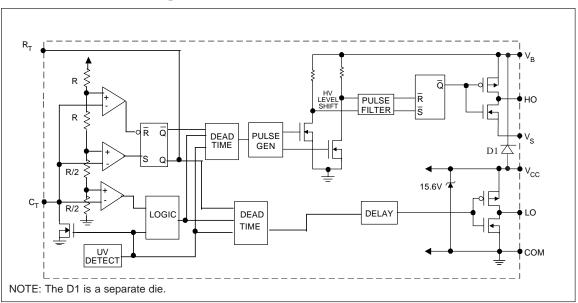


NOTE: The IR21531D is offered in 8 lead PDIP only.

# Functional Block Diagram for IR21531(S)

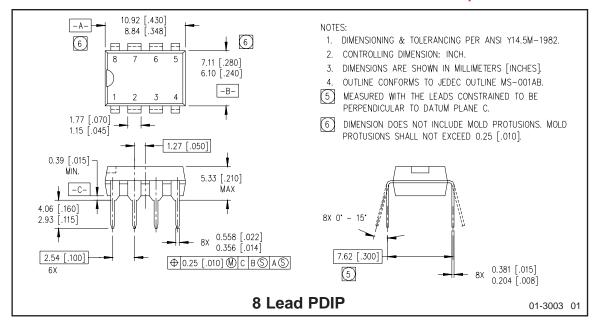


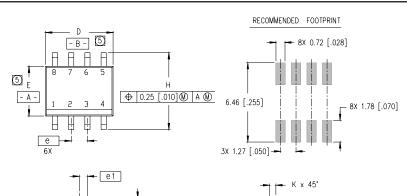
# Functional Block Diagram for IR21531D



# IR21531(D)(S) & (PbF)

NOTE: For new designs, we recommend IR's new product IRS21531D





0.10 [.004]

DIM	INCHES		MILLIME	TERS
DIM	MIN	MAX	MIN	MAX
Α	.0532	.0688	1.35	1.75
A1	.0040	.0098	0.10	0.25
В	.014	.018	0.36	0.46
С	.0075	.0098	0.19	0.25
D	.189	.196	4.80	4.98
Ε	.150	.157	3.81	3.99
е	.050 B	ASIC	1.27 BASIC	
e 1	.025 B	ASIC	0.635	BASIC
Н	.2284	.2440	5.80	6.20
K	.011	.019	0.28	0.48
L	.016	.050	0.41	1.27
У	0.	8.	0.	8.

#### NOTES:

- C -

- 1. DIMENSIONING & TOLERANCING PER ANSI Y14.5M-1982.
- 2. CONTROLLING DIMENSION: MILLIMETER.

→ | 0.25 [.010] M | C | A S | B S |

- 3. DIMENSIONS ARE SHOWN IN MILLIMETERS [INCHES].
- 4. OUTLINE CONFORMS TO JEDEC OUTLINE MS-012AA.
- DIMENSION DOES NOT INCLUDE MOLD PROTRUSIONS.
  MOLD PROTRUSIONS NOT TO EXCEED 0.25 [.006].
- (6) DIMENSION IS THE LENGTH OF LEAD FOR SOLDERING TO A SUBSTRATE.

#### 8 Lead SOIC

(6)

01-0021 08

# IR21531(D)(S) & (PbF) NOTE:For new designs, we recommend IR's new product IRS21531D

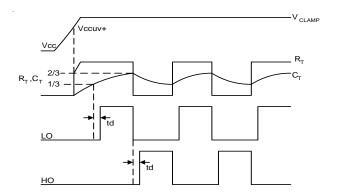


Figure 1. Input/Output Timing Diagram

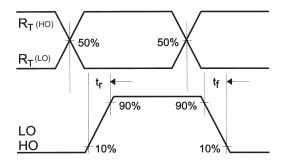


Figure 2. Switching Time Waveform Definitions

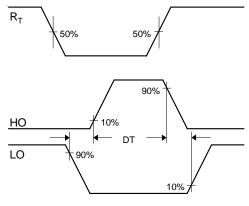
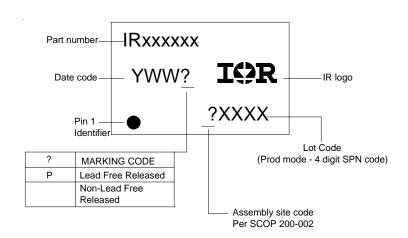


Figure 3. Deadtime Waveform Definitions

#### LEADFREE PART MARKING INFORMATION



### **ORDER INFORMATION**

#### **Basic Part (Non-Lead Free)**

8-Lead PDIP IR21531 order IR21531 8-Lead SOIC IR21531S order IR21531S 8-Lead PDIP IR21531D order IR21531D

#### Leadfree Part

8-Lead PDIP IR21531 order IR21531PbF 8-Lead SOIC IR21531S order IR21531SPbF 8-Lead PDIP IR21531D order IR21531DPbF



IR WORLD HEADQUARTERS: 233 Kansas St., El Segundo, California 90245 Tel: (310) 252-7105

This product has been qualified per industrial level

Data and specifications subject to change without notice. 5/21/2020

# **Mouser Electronics**

**Authorized Distributor** 

Click to View Pricing, Inventory, Delivery & Lifecycle Information:

# Infineon:

IR21531DPBF IR21531PBF IR21531SPbF IR21531STRPBF